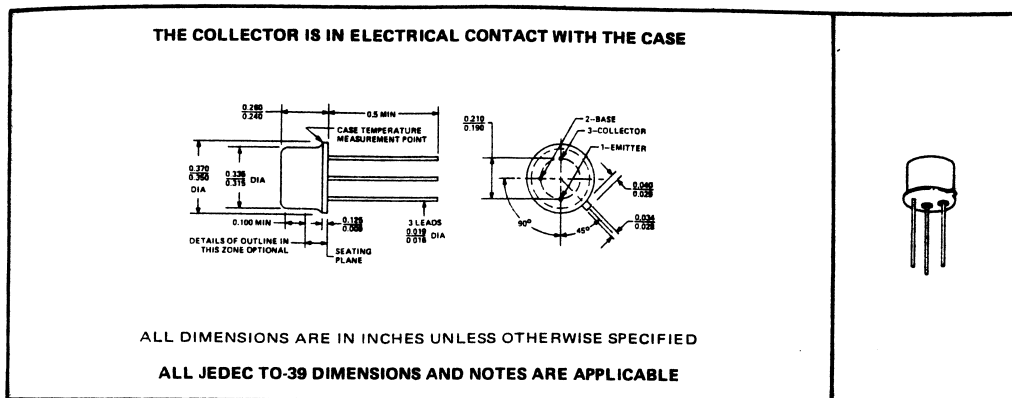


New Jersey Semi-Conductor Products, Inc.

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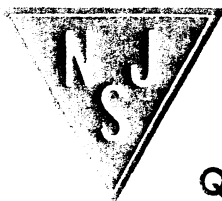
TYPES 2N6461 THRU 2N6464 **N-P-N SILICON TRANSISTORS**



*absolute maximum ratings at 25°C free-air temperature (unless otherwise noted)

	2N6461	2N6463
	2N6462	2N6464
Collector-Base Voltage	300 V	250 V
Collector-Emitter Voltage (See Note 1)	300 V	250 V
Emitter-Base Voltage	7 V	6 V
Continuous Collector Current	100 mA	100 mA
Continuous Device Dissipation at (or below) 25°C Free-Air Temperature (See Note 2)	1 W	1 W
Continuous Device Dissipation at (or below) 25°C Case Temperature (See Note 3)	10 W	10 W
Storage Temperature Range	-65°C to 200°C	-65°C to 200°C
Lead Temperature 1/16 Inch from Case for 10 Seconds	300°C	300°C

NOTES: 1. This value applies between 0 and 10 mA collector current when the base-emitter diode is open-circuited.
2. Derate linearly to 175°C free-air temperature at the rate of 6.67 mW/°C.
3. Derate linearly to 175°C case temperature at the rate of 66.7 mW/°C.



Quality Semi-Conductors

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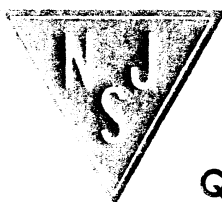
TYPES 2N6461 THRU 2N6464
N-P-N SILICON TRANSISTORS

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*electrical characteristics at 25°C free-air temperature (unless otherwise noted)

PARAMETER	TEST CONDITIONS	2N6461		2N6462		2N6463		2N6464		UNIT
		MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
V(BR)CBO Collector-Base Breakdown Voltage	I _C = 100 μ A, I _E = 0	300		300		250		250		V
V(BR)CEO Collector-Emitter Breakdown Voltage	I _C = 10 mA, I _B = 0, See Note 4	300		300		250		250		V
V(BR)EBO Emitter-Base Breakdown Voltage	I _E = 100 μ A, I _C = 0	7		7		6		6		V
I _{CBO} Collector Cutoff Current	V _{CB} = 200 V, I _E = 0		50		50					nA
	V _{CB} = 150 V, I _E = 0					50		50		nA
	V _{CB} = 200 V, I _E = 0, T _A = 125°C		20		20					μ A
	V _{CB} = 150 V, I _E = 0, T _A = 125°C					20		20		μ A
	V _{EB} = 5 V, I _C = 0	10		10		10		10		nA
h _{FE} Static Forward Current Transfer Ratio	V _{CE} = 10 V, I _C = 4 mA	20		20		20		20		
	V _{CE} = 10 V, I _C = 20 mA, See Note 4	30	120	100	300	30	120	100	300	
	V _{CE} = 10 V, I _C = 40 mA, See Note 4					30		40		
V _{BE} Base-Emitter Voltage	V _{CE} = 10 V, I _C = 20 mA, See Note 4	1		1		1		1		V
V _{CE(sat)} Collector-Emitter Saturation Voltage	I _B = 2 mA, I _C = 20 mA, See Note 4	1.1		1.1		1		1		V
h _{fe1} Small-Signal Common-Emitter Forward Current Transfer Ratio	V _{CE} = 20 V, I _C = 20 mA, f = 20 MHz	3.5	10	3.5	10	3.5	10	3.5	10	
C _{cb} Collector-Base Capacitance	V _{CB} = 20 V, I _E = 0, f = 1 MHz, See Note 5	3		3		3		3		pF

NOTES: 4. These parameters must be measured using pulse techniques. $t_w = 300 \mu$ s, duty cycle $\leq 2\%$.
5. C_{cb} measurement employs a three-terminal capacitance bridge incorporating a guard circuit. The emitter is connected to the guard terminal of the bridge.



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